On-substrate polymerization – a versatile approach for preparing conjugated polymers suitable as electrochromes and metal ion sensing

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Figure S2. Percent transmission of P1 monitored at 690 nm with switching potentials of 1500 and 100 mV for 40 and 5 sec.



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Figure S6. Dependence of Δi on the thickness of the layer of **P1**.



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Figure S8. Dependence of ΔE on the thickness of the layer of **P1**.



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Figure S12. Profilometry trace of P1 immobilized on glass having a thickness of 500 nm.



Figure S13. Profilometry trace of P1 immobilized on glass having a thickness of 350 nm.



Figure S14. Profilometry trace of P1 immobilized on glass having a thickness of 130 nm.



Figure S15. Spectroelectrochemistry of **P2** with applied voltages of 0 (—), 800 (—), 1000 (—), 1100 (—), 1200 (—), 1300 (—), 1400 (—), and 1500 (—) mV for 30 sec.



Figure S16. Spectroelectrochemistry of **P2** with applied voltages of 1500 (—), 1400 (—), 1300 (—), 1200 (—), 1100 (—), 1000 (—), 800 (—), 600 (—), 400 (—), and 0 (—) mV for 30 sec



Figure S17. Transmission percent with switching potentials of 1300 and 100 mV for 20, 15, 10, 5 and 1 sec monitored at 720 nm for **P2**.



Figure S18. The UV-Vis spectra of polymer P2 in its original (—), oxidized (—) and neutral (—) states.



Figure S19. Dependence of cyclic voltammograms on the thickness of the layer of **P2** immobilized on ITO glass slides: 2000 (—), 1500 (—), 900 (—), 500 (—), 400 (—), 280 (—) and 130 (—) nm measured in anhydrous deaerated acetonitrille with 0.1 M TBAPF₆.



Figure S20. Dependence of i_{ox} on the thickness of the layer for **P2** (R = 0.96).



Figure S21. Dependence of i_{rev} on the thickness of the layer for **P2** (R = -0.96).



Figure S22. Dependence of Δi on the thickness of the layer of **P2** (R = 0.96).



Figure S23. Dependence of i_{ox}/i_{rev} on the thickness of the layer of **P2**.



Figure S24. Dependence of ΔE on the thickness of the layer of P2 (R = 0.98).



Figure S25. Spectroelectrochemistry of **P3** with applied voltages of 0 (—), 900 (—), 1000 (—), 1100 (—), 1200 (—), 1300 (—), 1400 (—), 1500 (—), 1600 (—), 1700 (—) and 1800 (—) mV for 30 sec.



Figure S26. Spectroelectrochemistry of **P3** with applied voltages of 1800 (—), 1600 (—), 1400 (—), 1200 (—), 1000 (—), 800 (—), 600 (—), and 0 (—) mV for 30 sec.



Figure S27. Percent transmission of P3 monitored at 700 nm with switching potentials of 1500 and 100 mV for 20, 15, 10, 5 and 1 sec.



Figure S28. Absorbance spectra of P3 in its original (—), oxidized (—) and neutral (—) states.



Figure S29. Dependence of cyclic voltammograms on the thickness of the layer of P3 immobilized on ITO glass slides: 2500 (—), 1000 (—), 720 (—), 400 (—), 300 (—), 200 (—) and 120 (—) nm measured in anhydrous degased acetonitrlle with 0.1 M TBAPF₆.



Figure S30. Dependence of i_{ox} on the thickness of the layer for **P3**.



Figure S31. Dependence of i_{rev} on the thickness of the layer for P3



Figure S32. Dependence of Δi on the thickness of the layer of **P3**.



Figure S33. Dependence of i_{ox}/i_{rev} on the thickness of the layer of **P3**.



Figure S34. Dependence of ΔE on the thickness of the layer of **P3**.



Figure S35. Complexation of P1 (top), P2 (middle) and P3 (bottom) with various transition metal ions before (left) and after heating at 65°C for 2h (right).

Cu(BF ₄) ₂	Cu(ClO ₄) ₂	Cu(OAc) _z	ZnCl ₂	Zn(CF ₅ SO ₅) ₂	Zn(ClO ₄) _z	RuCl ₃
Fe(BF ₄) ₂	Fe(CF ₃ SO ₃) ₃	FeBr ₃	Fe(ClO ₄) ₃	Co(ClO ₄) ₂	CoCl ₂	AgBF₄
AgPFa	EuCl ₅	Ni(NO ₃) ₂	Cul	Pb(OAc) ₂	Hg(OAC) ₂	Original polymer

Figure S36. Corresponding legend of metal ion complexes drop-casted onto polymers from Figure 29.



Figure S37. Absorbance spectra of complexes of **P1** immobilized on ITO coated glass with dropcast Cu(BF₄)₂ (—), Cu(ClO₄)₂ (—),Cu(OAc)₂ (—), ZnCl₂ (—), Zn(OTf)₂ (—), Zn(ClO₄)₂ (—), RuCl₃ (—), Fe(BF₄)₂ (—), Fe(OTf)₂ (—), FeBr₃ (—), Fe(ClO₄)₃ (—), Co(ClO₄)₂ (—), CoCl₂ (—), AgBF₄ (—), AgPF₆ (—), EuCl₃ (—), Ni(NO₃)₂ (—), CuI (—), Pb(OAc)₂ (—) and Hg(OAc)₂ (—) measured after heating at 65°C for 2h.

Salts.					
metal salt	λ_{abs} (nm)	metal salt	$\lambda_{abs} (nm)$	metal salt	$\lambda_{abs} (nm)$
Cu(BF ₄) ₂	504	$Fe(BF_4)_2$	535	AgPF ₆	458
$Cu(ClO_4)_2$	459	Fe(OTf) ₂	466	EuCl ₃	439
$Cu(OAc)_2$	444	FeBr ₃	468	$Ni(NO_3)_2$	452
ZnCl ₂	451	$Fe(ClO_4)_3$	696	CuI	467
$Zn(OTf)_2$	460	$Co(ClO_4)_2$	442	$Pb(OAc)_2$	455
$Zn(ClO_4)_2$	460	CoCl ₂	448	$Hg(OAc)_2$	458
RuCl ₃	459	$AgBF_4$	445	,	

Table S1. Absorbance maximum of P3 immobilized on ITO coated glass with various metal salts

		J		0		J	
	i_{ox} (mA)	i_{rev} (mA)	⊿i (mA)	i_{ox}/i_{rev}	$E_{ox}(V)$	$E_{rev}(V)$	$\Delta E(V)$
1500 nm	-	-0.61	-	-	-	1.40	-
1000 nm	4.15	-0.51	4.66	-8.14	1.70	1.14	0.56
750 nm	3.45	-0.67	4.12	-5.15	1.64	1.19	0.45
500 nm	3.55	-1.64	5.19	-2.16	1.83	1.05	0.78
350 nm	4.10	-2.61	6.71	-1.57	1.57	0.95	0.62
130 nm	1.44	-0.71	2.15	-2.03	1.50	1.05	0.45

Table S2. Dependence of anodic cyclic voltammograms on the thickness of the layer of P1.

Table S3. Dependence of cyclic voltammograms on the thickness of the layer of P2.

	i_{ox} (mA)	i_{rev} (mA)	$\Delta i (mA)$	i_{ox}/i_{rev}	$E_{ox}(V)$	$E_{rev}(V)$	$\Delta E(V)$
2000 nm	7.79	-1.68	9.47	-4.64	1.78	0.92	0.86
1500 nm	7.13	-1.15	8.28	-6.20	1.70	1.01	0.69
900 nm	4.98	-1.00	5.98	-4.98	1.58	1.00	0.58
500 nm	4.69	-0.79	5.48	-5.94	1.54	1.03	0.51
400 nm	3.30	-0.55	3.85	-6.00	1.45	0.98	0.47
280 nm	2.61	-0.39	3.00	-6.69	1.40	1.06	0.34
130 nm	1.57	-0.13	1.70	-12.08	1.30	0.93	0.37

Table S4. Dependence of cyclic voltammograms on the thickness of the layer of P3.

	i_{ox} (mA)	i_{rev} (mA)	$\Delta i (\mathrm{mA})$	i _{ox} /i _{rev}	$E_{ox}(V)$	$E_{rev}(V)$	$\Delta E(V)$
2500 nm	7.23	0.21	7.02	34.43	1.87	1.25	0.62
1000 nm	7.43	-0.57	8.00	-13.03	1.92	1.21	0.71
720 nm	3.85	-0.23	4.08	-16.74	1.63	1.23	0.40
400 nm	1.47	-0.69	2.16	-2.13	1.53	1.13	0.40
300 nm	1.69	-0.77	2.46	-2.19	1.52	1.08	0.44
200 nm	1.36	-0.31	1.67	-4.39	1.54	1.07	0.47
120 nm	0.52	-0.11	0.63	-4.73	1.40	1.04	0.36



Figure S38. ¹H NMR spectrum of 1.



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Figure S41. ¹³C NMR spectrum of 2.



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